

	L #	Hits	Search Text	DBs
1	L1	304087	"257"/\$.cccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
2	L3	697	2 and (charge near trap\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
3	L6	0	5 and fin	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
4	L4	0	3 and (dop\$3 near fin)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
5	L8	56	(park-sheung-hee or fastow-richard-m or ju- dong-hyuk).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
6	L10	0	8 and (dop\$3 near fin)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
7	L2	8796	1 and (non-volatile or flash) near (memory or device)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
8	L5	11	3 and dop\$3 near (float\$3 near gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
9	L7	0	5 and (reduc\$3 near leakage near current)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
10	L11	20503	((non-volatile or flash) near (memory or device)).ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
11	L13	0	12 and dop\$3 near (float\$3 near gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
12	L14	0	12 and (fin or fin-shape) near (float\$3 near gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
13	L15	120791	((non-volatile or flash) near (memory or device))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
14	L12	6	11 and (reduc\$3 near leakage near current).ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
15	L16	137	15 and dop\$3 near (float\$3 near gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
16	L17	1	16 and (reduc\$3 near leakage near current)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB